

In th Specification

At page 1, after the title, insert:

CROSS REFERENCE TO RELATED APPLICATION

This patent application is a Continuation of U.S. Patent Application Serial No. 08/886,388 filed July 16, 1997, entitled "Method of Forming a Capacitor and a Capacitor Construction", naming Gurtej S. Sandhu and Pierre C. Fazan as inventors, which is a divisional application of United States Patent Application Serial No. 08/582,385, which was filed January 3, 1996, now U.S. Patent No. 6,218,237.

In the Claims

Cancel claims 1-45 and add new claims 46-60 as shown below.

New Claims

46. A pair of adjacent stacked capacitors fabricated on a semiconductor substrate, the adjacent stacked capacitors respectively each including:

A1 a polycrystalline silicon lower plate, the lower plates having a minimum lateral spacing from one another that is less than a minimum photolithographic feature dimension with which the capacitors are fabricated; and

a plug extending below the plate and having a diameter less than the minimum photolithographic feature dimension.